

# DATA SHEET

## **PDTC144T series**

NPN resistor-equipped transistors;  
R1 = 47 k $\Omega$ , R2 = open

Product specification  
Supersedes data of 2002 Mar 15

2003 Apr 14

## NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

## PDTC144T series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	47	–	k $\Omega$
R2	open	–	–	–

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE
	PHILIPS	EIAJ	
PDTC144TEF	SOT490	SC-89	33
PDTC144TK	SOT346	SC-59	53
PDTC144TM	SOT883	SC-101	E4
PDTC144TS	SOT54 (TO-92)	SC-43	TC144T
PDTC144TT	SOT23	–	*41 <sup>(1)</sup>
PDTC144TU	SOT323	SC-70	*41 <sup>(1)</sup>

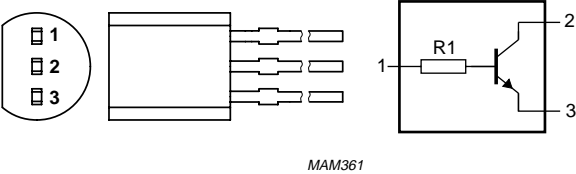
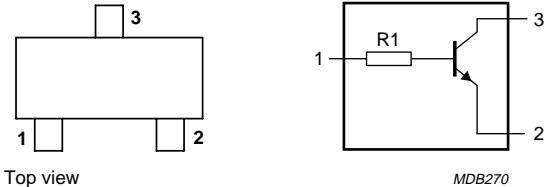
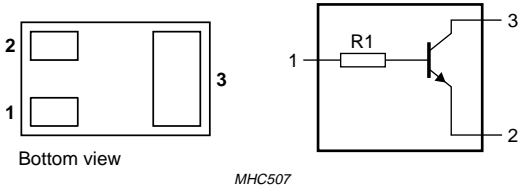
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistors;  
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PDTC144T series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC144TS	 MAM361	1 2 3	base collector emitter
PDTC144TEF PDTC144TK PDTC144TT PDTC144TU	 Top view MDB270	1 2 3	base emitter collector
PDTC144TM	 Bottom view MHC507	1 2 3	base emitter collector

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### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

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## CHARACTERISTICS

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>C</sub> = 0	–	–	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	–	–	1	$\mu$ A
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	–	–	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA	100	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	–	–	150	mV
R1	input resistor		33	47	61	k $\Omega$
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	–	–	2.5	pF

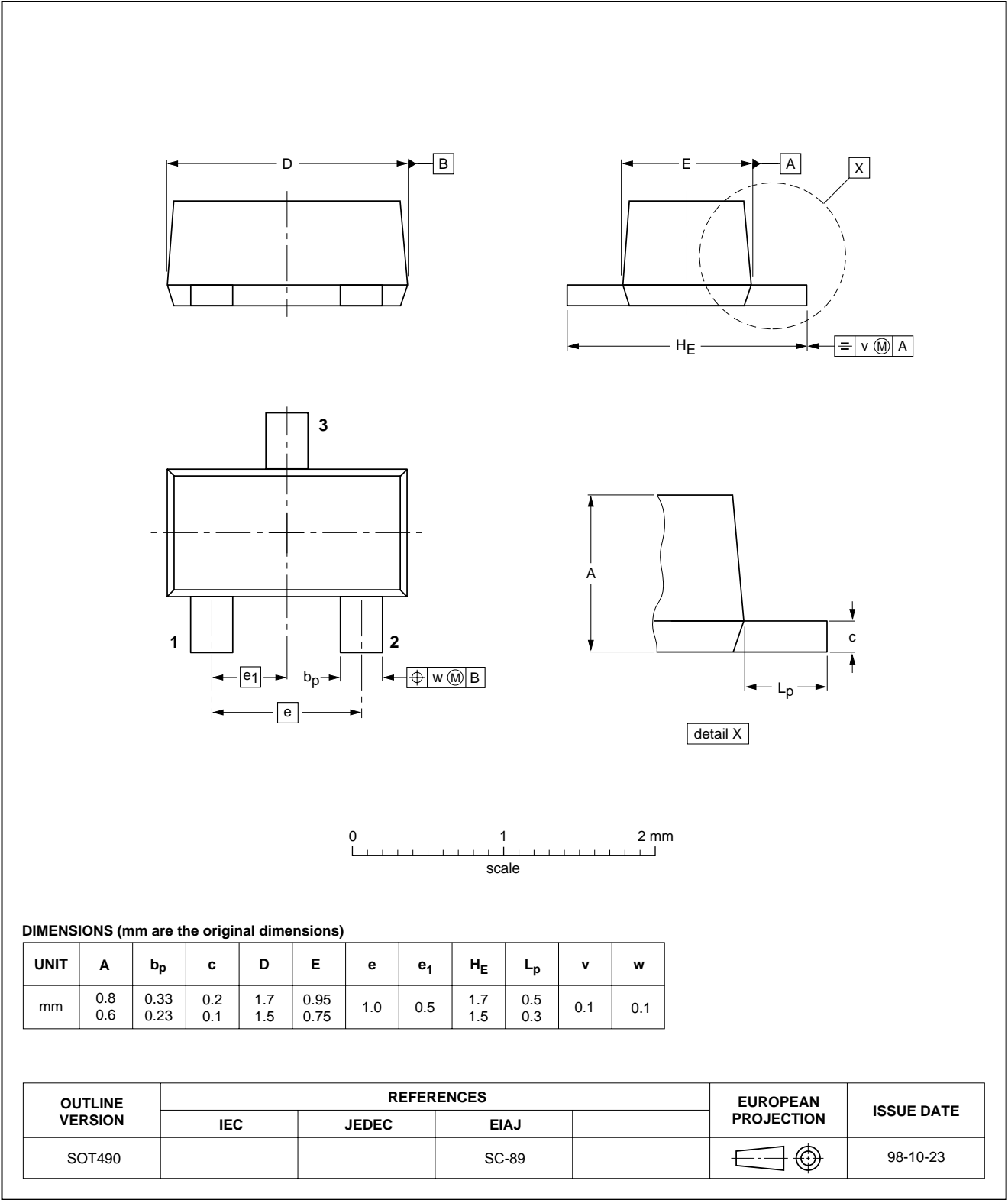
NPN resistor-equipped transistors;  
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PDTC144T series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT490

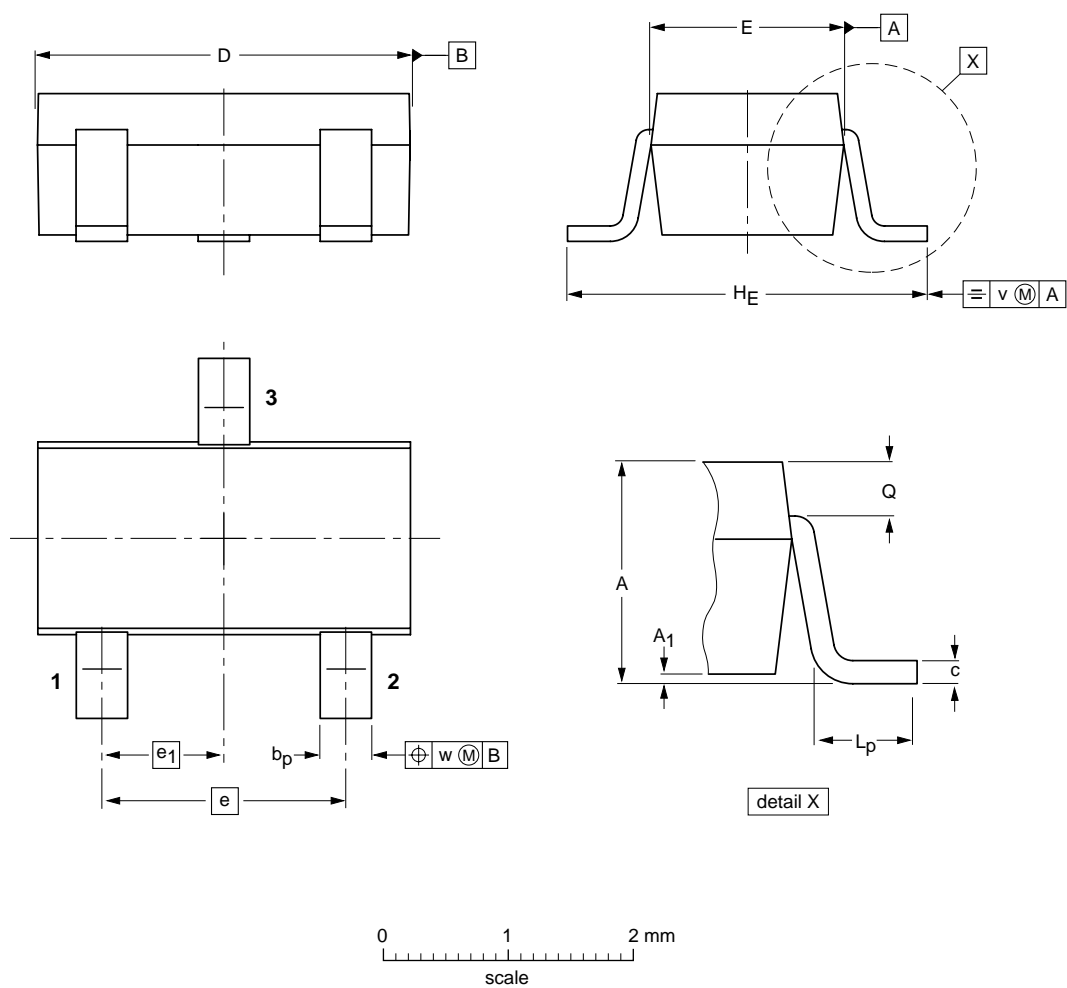


NPN resistor-equipped transistors;  
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PDTC144T series


Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

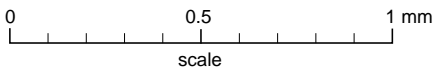
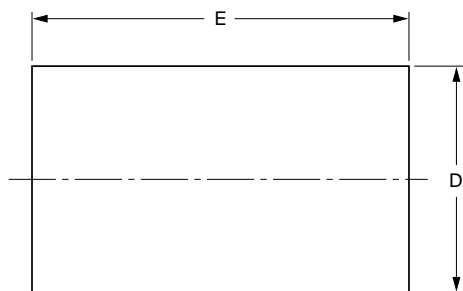
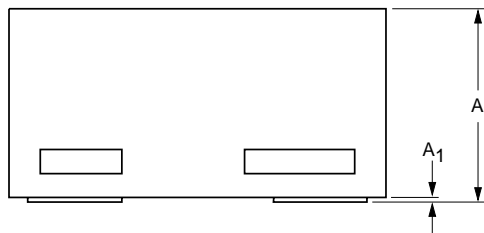
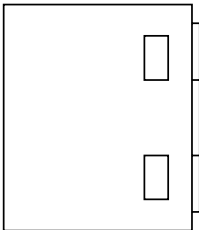
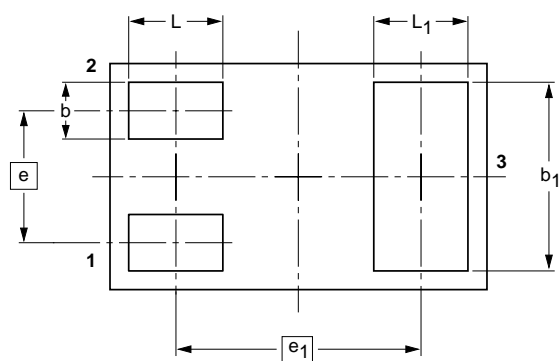
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

NPN resistor-equipped transistors;  
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PDTC144T series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883




DIMENSIONS (mm are the original dimensions)

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

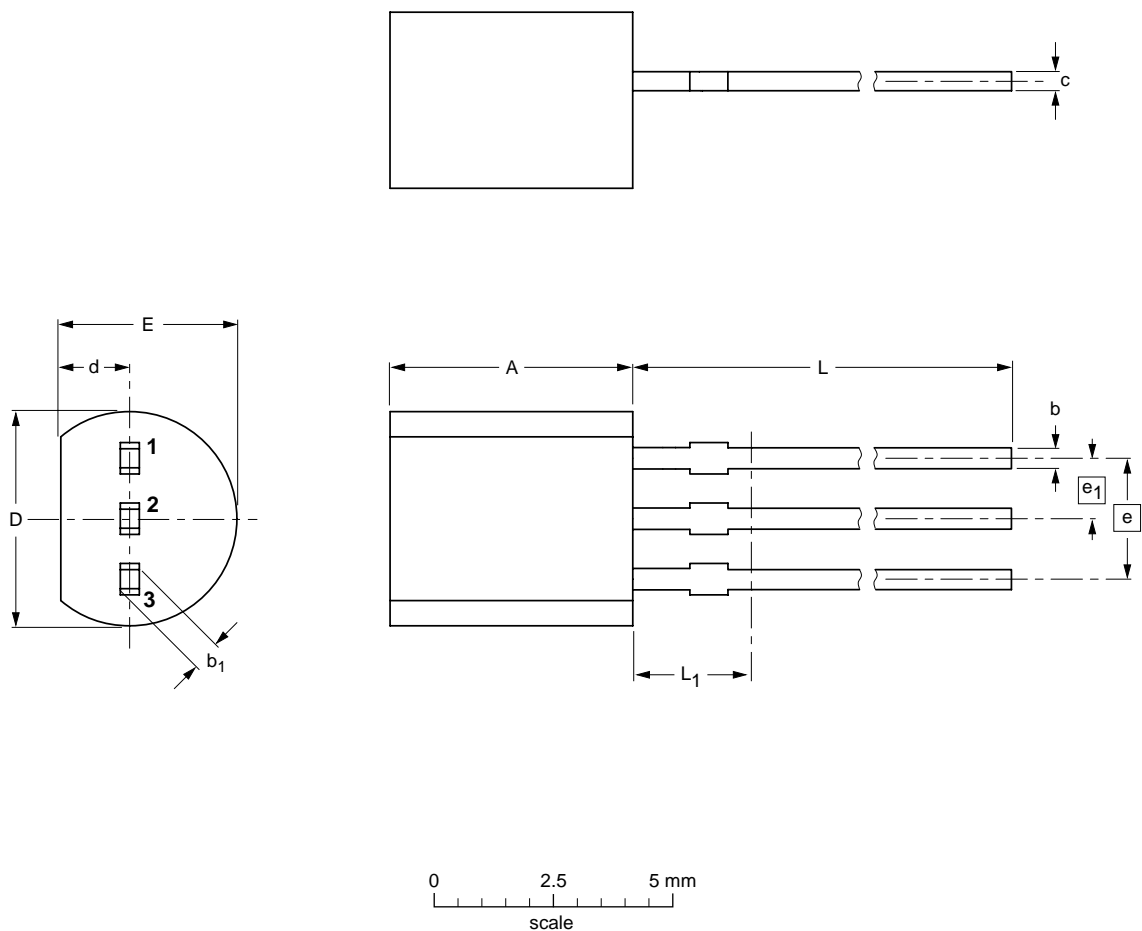
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			03-02-05 03-04-03

NPN resistor-equipped transistors;  
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PDTC144T series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54




DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

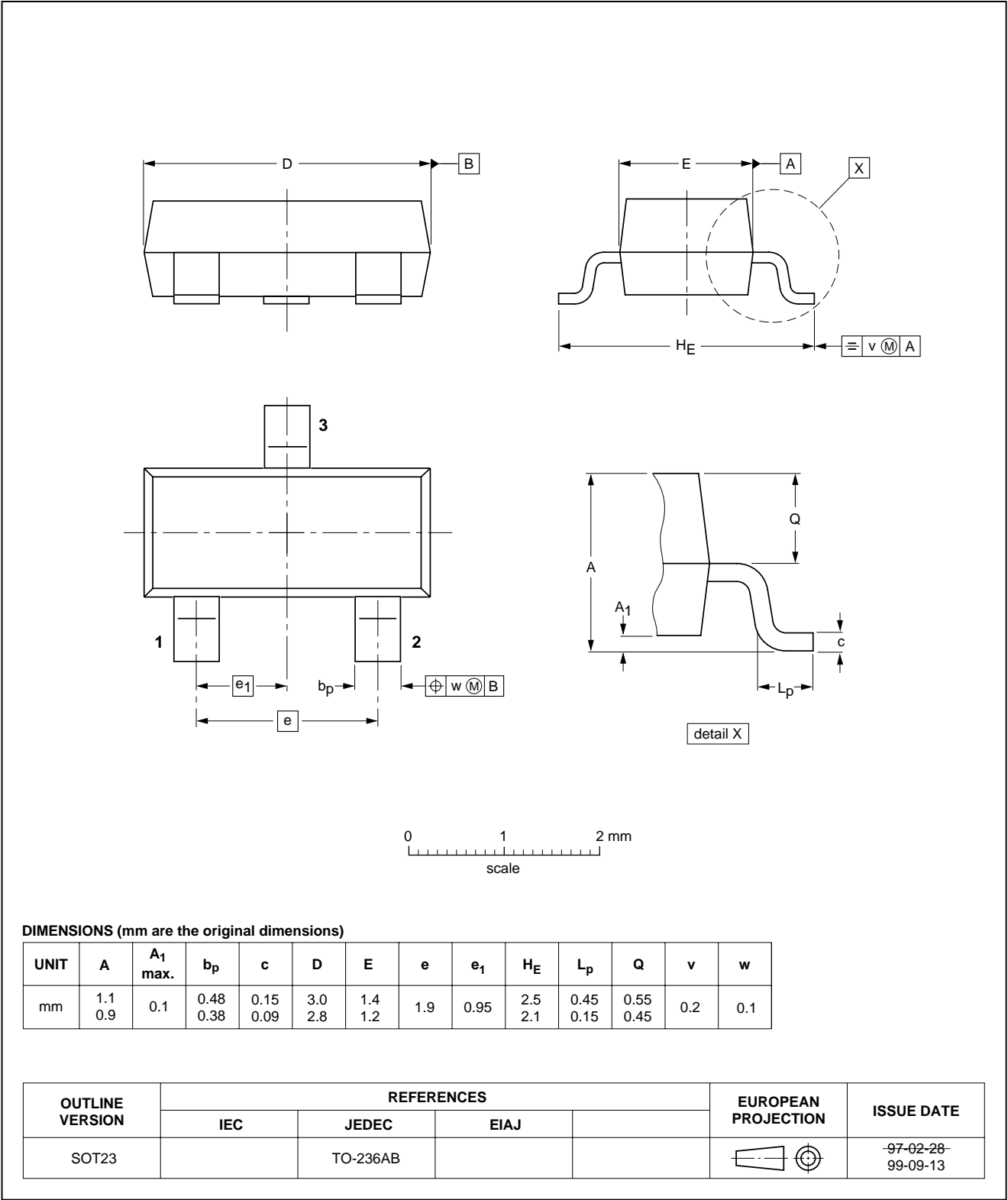
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	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28

NPN resistor-equipped transistors;  
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PDTC144T series

Plastic surface mounted package; 3 leads

SOT23

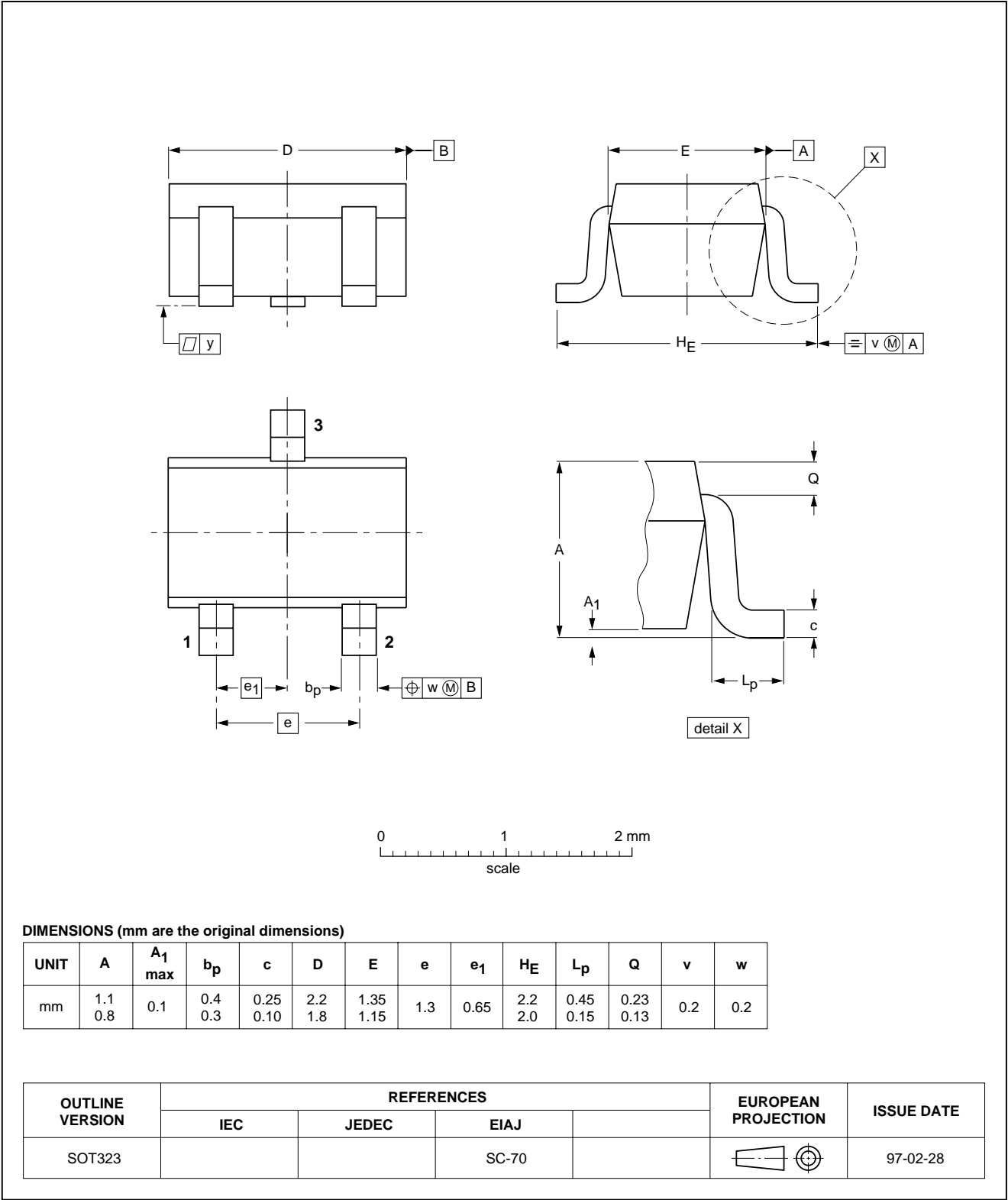


NPN resistor-equipped transistors;  
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PDTC144T series

Plastic surface mounted package; 3 leads

SOT323



NPN resistor-equipped transistors;  
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**NOTES**

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